

TENTATIVE TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC5318

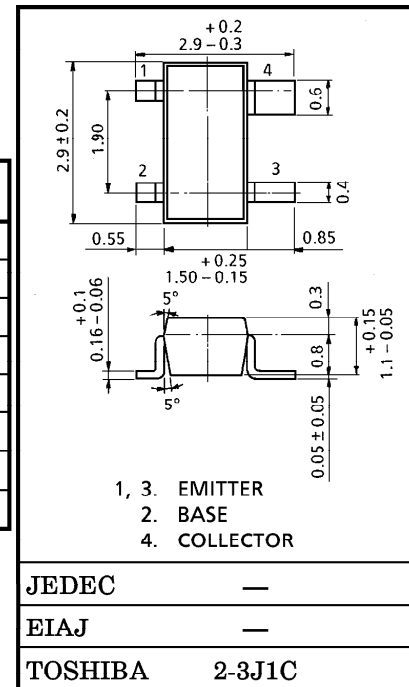
VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

- Low Noise Figure : NF = 1.3dB (f=2GHz)
- High Gain : Ga = 11.5dB (f=2GHz)

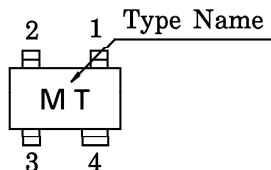
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	8	V
Collector-Emitter Voltage	V _{CEO}	5	V
Emitter-Base Voltage	V _{EB0}	1.5	V
Collector Current	I _C	20	mA
Base Current	I _B	10	mA
Collector Power Dissipation	P _C	150	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55~125	°C



Weight : 0.012g

Marking



MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f _T	V _{CE} = 3V, I _C = 15mA	13	16	—	GHz
Insertion Gain	S _{21e} ² (1)	V _{CE} = 3V, I _C = 15mA, f = 1GHz	14.5	17	—	dB
	S _{21e} ² (2)	V _{CE} = 3V, I _C = 15mA, f = 2GHz	8.5	11.5	—	
Noise Figure	NF (1)	V _{CE} = 3V, I _C = 5mA, f = 1GHz	—	0.9	1.8	dB
	NF (2)	V _{CE} = 3V, I _C = 5mA, f = 2GHz	—	1.3	2.2	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = 10V, I _E = 0	—	—	1	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} = 1V, I _C = 0	—	—	1	μA
DC Current Gain	h _{FE}	V _{CE} = 3V, I _C = 15mA	50	—	250	V
Output Capacitance	C _{ob}	V _{CB} = 2.5V, I _E = 0, f = 1MHz	—	0.6	—	pF
Reverse Transfer Capacitance	C _{re}	(Note)	—	0.4	—	pF

(Note) : C_{re} is measured by 3 terminal method with Capacitance Bridge.

CAUTION : This device electrostatic sensitivity. Please handle with caution.

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